

Vishay Siliconix

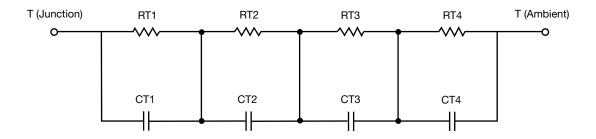
R-C Thermal Model Parameters

DESCRIPTION

The parametric values in the R-C thermal model have been derived using curve-fitting techniques. R-C values for the electrical circuit in the Foster/tank and Cauer/filter configurations are included. When implemented in PSpice, these values have matching characteristic curves to the single-pulse transient thermal impedance curves for the MOSFET.

These RC values can be used in the PSpice simulation to evaluate the thermal behavior of the MOSFET junction temperature under a defined power profile. These techniques are described in application note AN609, "Thermal Simulation of Power MOSFETs on the PSpice Platform".

R-C THERMAL MODEL FOR TANK CONFIGURATION



R-C VALUES FOR TANK	CONFIGURATION		
	THERMAL RES	SISTANCE (°C/W)	
Junction to	Ambient	Case	Foot
RT1	n/a	154.0171m	n/a
RT2	n/a	219.1530m	n/a
RT3	n/a	32.0078m	n/a
RT4	n/a	44.8221m	n/a
	THERMAL CAPAC	ITANCE (Joules/°C)	
Junction to	Ambient	Case	Foot
CT1	n/a	38.1462m	n/a
CT2	n/a	132.1102m	n/a
CT3	n/a	20.7480m	n/a
CT4	n/a	719.7175m	n/a

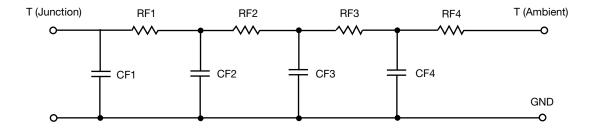
Note

n/a indicates not applicable

This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits.

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R-C THERMAL MODEL FOR FILTER CONFIGURATION



THERMAL RESISTANCE (°C/W)					
Junction to	Ambient	Case	Foot		
RF1	n/a	15.7853m	n/a		
RF2	n/a	84.5567m	n/a		
RF3	n/a	159.0351m	n/a		
RF4	n/a	190.6229m	n/a		
	THERMAL CAPAC	ITANCE (Joules/°C)			
Junction to	Ambient	Case	Foot		
CF1	n/a	11.0683m	n/a		
CF2	n/a	3.1891m	n/a		
CF3	n/a	17.2573m	n/a		
CF4	n/a	97.8060m	n/a		

Note

• n/a indicates not applicable



IRFP460B, SiHG460B_RC

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